

FS30AS-2

High-Speed Switching Use
Nch Power MOS FET

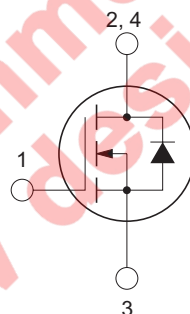
REJ03G1411-0200
(Previous: MEJ02G0100-0101)
Rev.2.00
Aug 07, 2006

Features

- Drive voltage : 10 V
- V_{DSS} : 100 V
- $r_{DS(ON) (max)}$: 100 m Ω
- I_D : 30 A
- Integrated Fast Recovery Diode (TYP.) : 95 ns

Outline

RENESAS Package code: PRSS0004ZA-A
(Package name: MP-3A)



1. Gate
2. Drain
3. Source
4. Drain

Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

(T_c = 25°C)

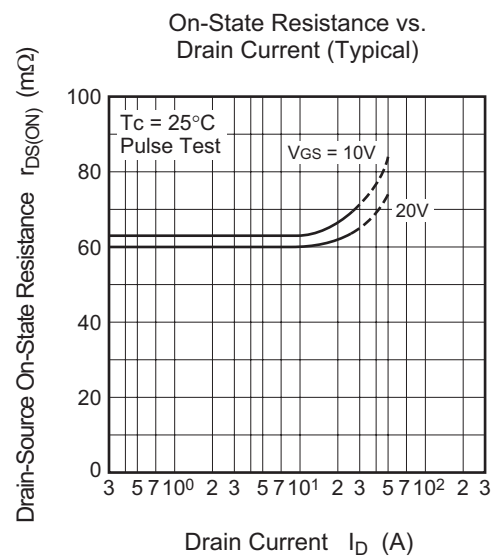
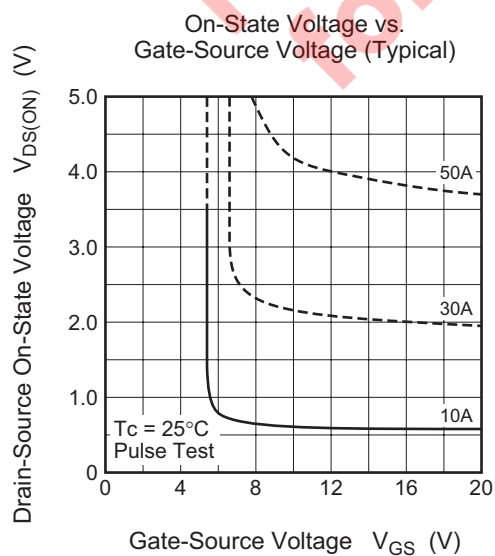
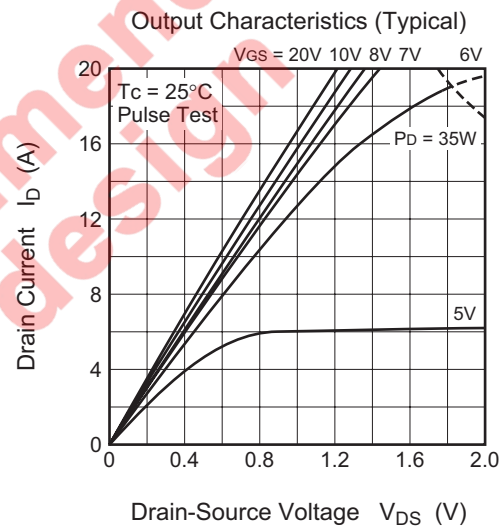
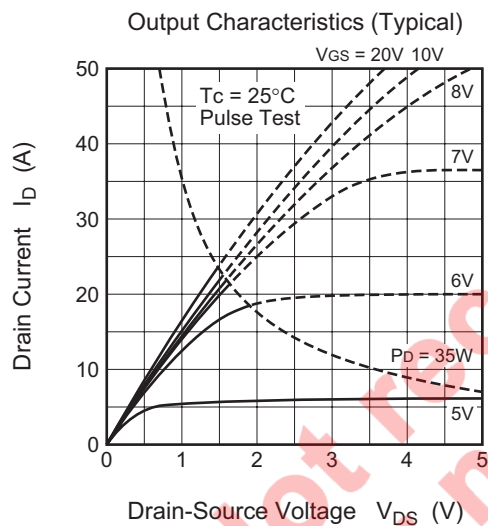
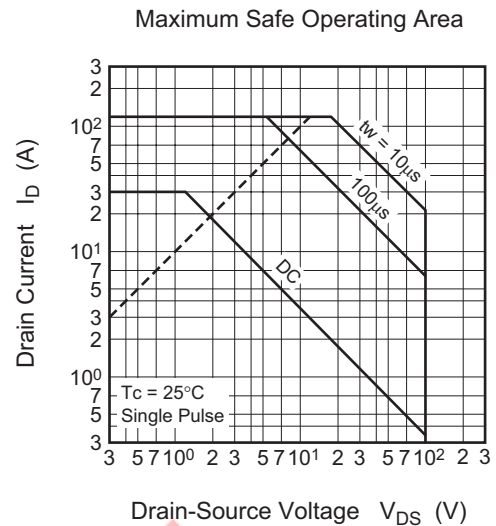
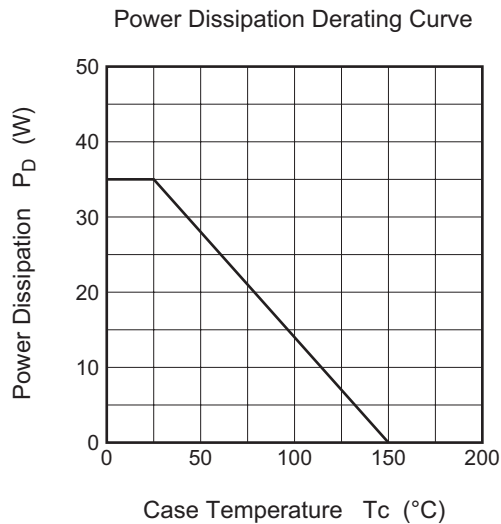
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	100	V	$V_{GS} = 0$ V
Gate-source voltage	V_{GSS}	±20	V	$V_{DS} = 0$ V
Drain current	I_D	30	A	
Drain current (Pulsed)	I_{DM}	120	A	
Avalanche drain current (Pulsed)	I_{DA}	30	A	L = 100 μ H
Source current	I_S	30	A	
Source current (Pulsed)	I_{SM}	120	A	
Maximum power dissipation	P_D	35	W	
Channel temperature	T _{ch}	– 55 to +150	°C	
Storage temperature	T _{stg}	– 55 to +150	°C	
Mass	—	0.32	g	Typical value

Electrical Characteristics

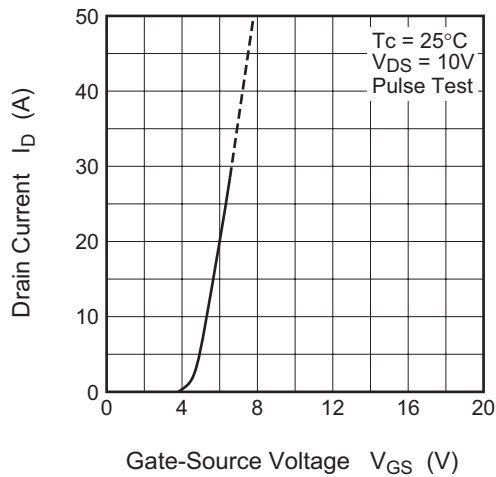
(Tch = 25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	0.1	mA	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	69	100	$\text{m}\Omega$	$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$
Drain-source on-state voltage	$V_{DS(ON)}$	—	1.04	1.50	V	$I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	18	—	S	$I_D = 15 \text{ A}$, $V_{DS} = 10 \text{ V}$
Input capacitance	C_{iss}	—	1250	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	230	—	pF	
Reverse transfer capacitance	C_{rss}	—	105	—	pF	
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	$V_{DD} = 50 \text{ V}$, $I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = R_{GS} = 50 \Omega$
Rise time	t_r	—	60	—	ns	
Turn-off delay time	$t_{d(off)}$	—	60	—	ns	
Fall time	t_f	—	50	—	ns	
Source-drain voltage	V_{SD}	—	1.0	1.5	V	$I_S = 15 \text{ A}$, $V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-c)}$	—	—	3.57	$^{\circ}\text{C/W}$	Channel to case
Reverse recovery time	t_{rr}	—	95	—	ns	$I_S = 30 \text{ A}$, $d_i/d_t = -100 \text{ A}/\mu\text{s}$

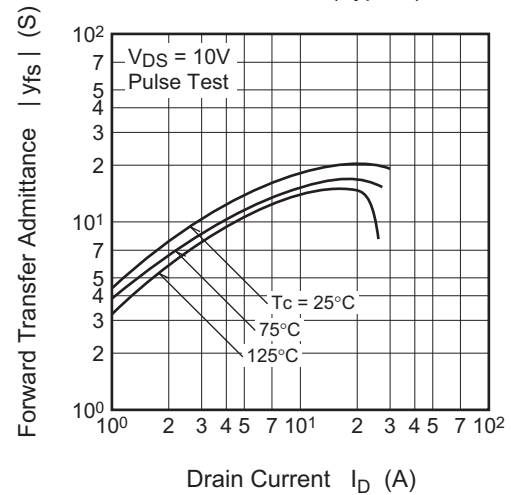
Performance Curves



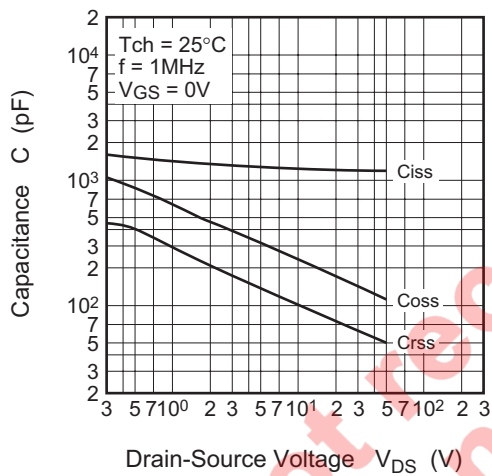
Transfer Characteristics (Typical)



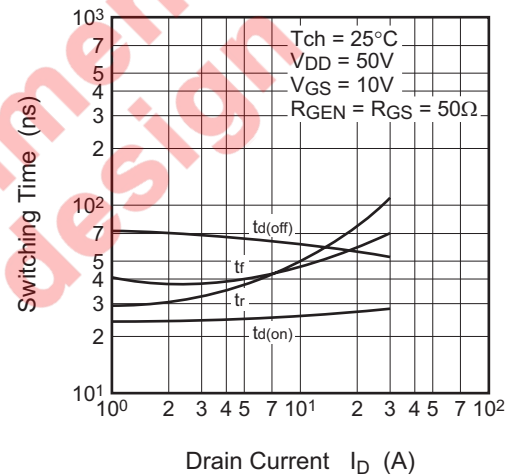
Forward Transfer Admittance vs. Drain Current (Typical)



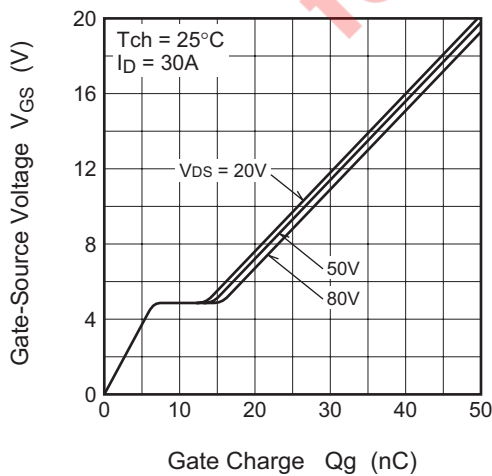
Capacitance vs. Drain-Source Voltage (Typical)



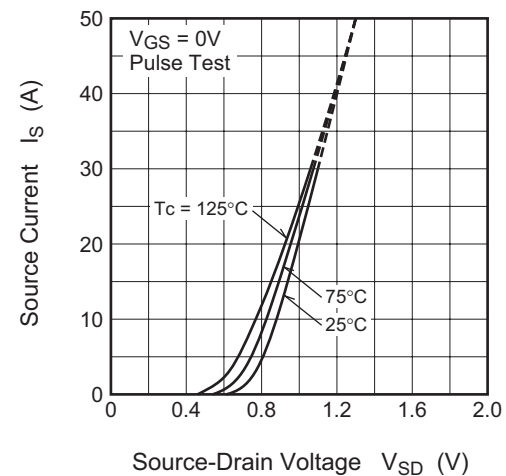
Switching Characteristics (Typical)

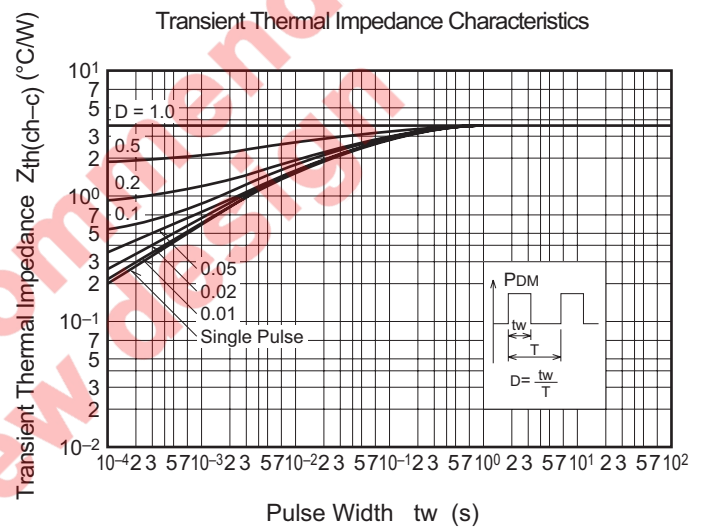
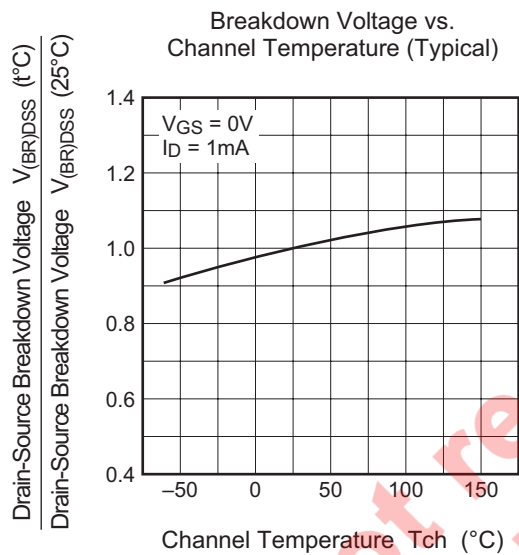
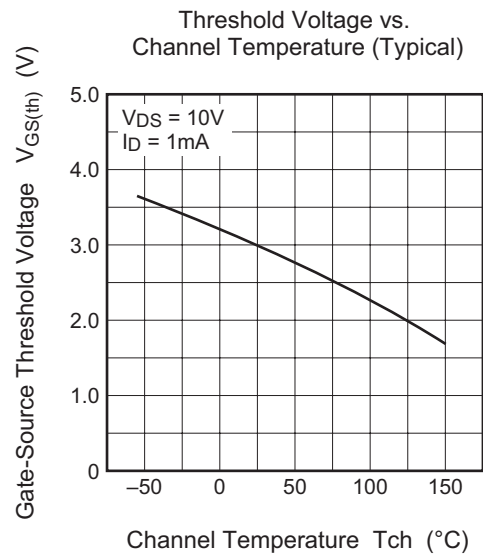
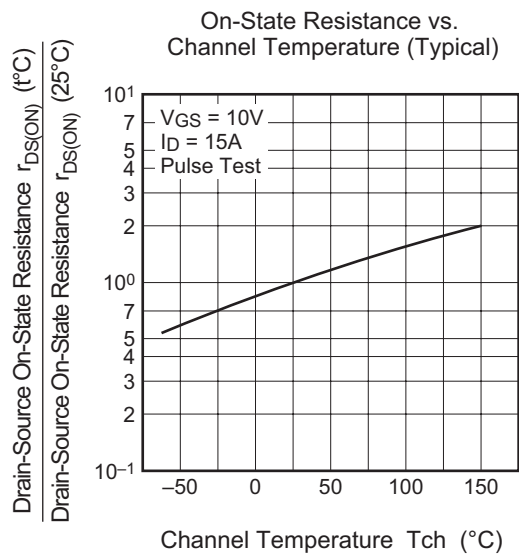


Gate-Source Voltage vs. Gate Charge (Typical)

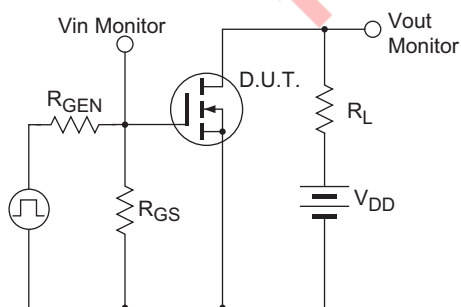


Source-Drain Diode Forward Characteristics (Typical)

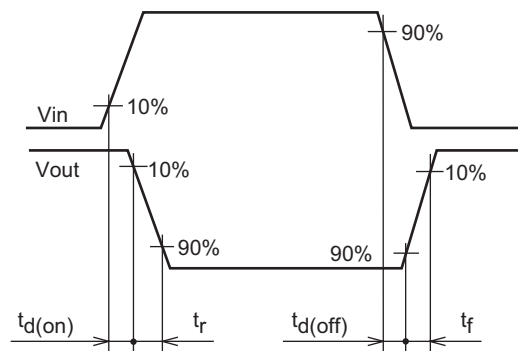




Switching Time Measurement Circuit



Switching Waveform



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
MP-3A	SC-63	PRSS0004ZA-A	—	0.32g	

The drawing shows three views of the FS30AS-2 package:

- Top View:** Dimensions include a total width of 6.6 mm, a central width of 5.3 ± 0.2 mm, a lead width of 1 ± 0.2 mm, a lead height of 6.1 ± 0.2 mm, and a maximum total height of 10.4 mm. The lead thickness is 0.76 mm, and the lead pitch is 2.3 ± 0.2 mm.
- Side View:** Dimensions include a lead height of 2.3 mm, a lead thickness of 0.5 ± 0.2 mm, a base thickness of 0.1 ± 0.1 mm, a lead length of 1.4 ± 0.2 mm, and a base width of 0.5 ± 0.2 mm.
- Bottom View:** Dimensions include a lead width of 2.3 mm and a lead thickness of 1 mm.

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS30AS-2-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS30AS-2

Note : Please confirm the specification about the shipping in detail.

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